

## General Description

The WST4045 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent  $R_{DS(on)}$  and gate charge for most of the synchronous buck converter applications .

The WST4045 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent  $CdV/dt$  effect decline
- 100% EAS Guaranteed
- Green Device Available

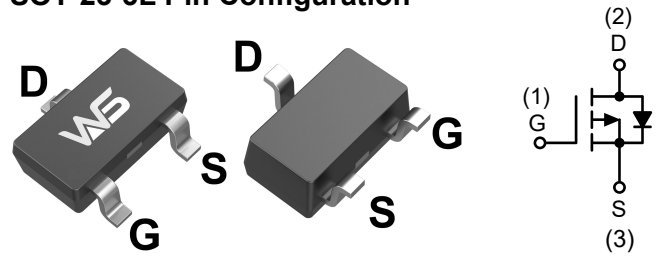
## Product Summary

$BV_{DSS}$	$R_{DS(on)}$	$I_D$
-40V	73mΩ	-4.3A

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

## SOT-23-3L Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-4.3	A
$I_{DP}$	Pulsed Drain Current	-20	A
$P_D$	Total Power Dissipation	2.0	W
TJ, TSTG	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	125	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 °C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	---	73	85	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A	---	98	126	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.5	-3.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.56	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-28V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =-28V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A	---	10	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	3.8	---	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.1A	---	14	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.9	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.8	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-20V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω, R <sub>L</sub> =2Ω	---	8	---	ns
T <sub>r</sub>	Rise Time		---	9	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	10	---	
T <sub>f</sub>	Fall Time		---	28	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, f=1MHz	---	650	---	pF
C <sub>oss</sub>	Output Capacitance		---	90	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	70	---	

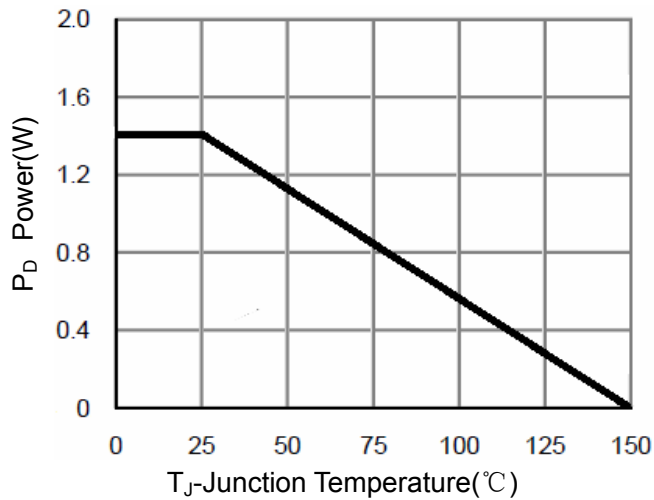
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-4.3	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-2.5A	---	---	-1.2	V

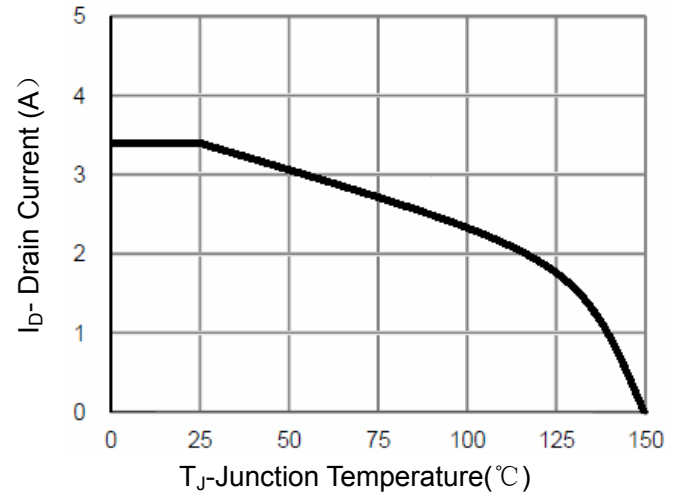
Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

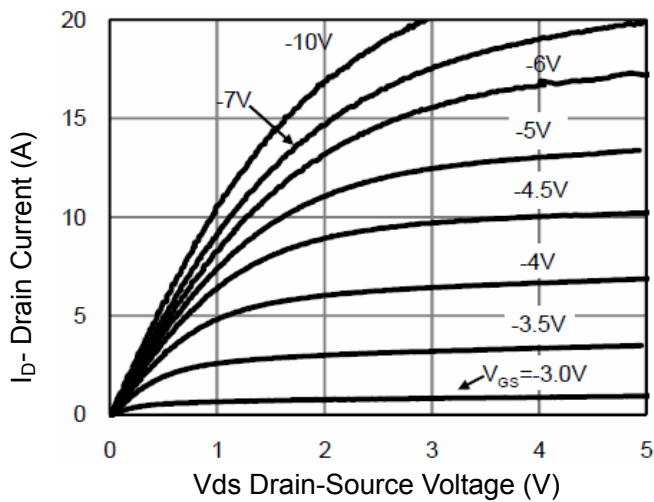
## Typical Electrical and Thermal Characteristics



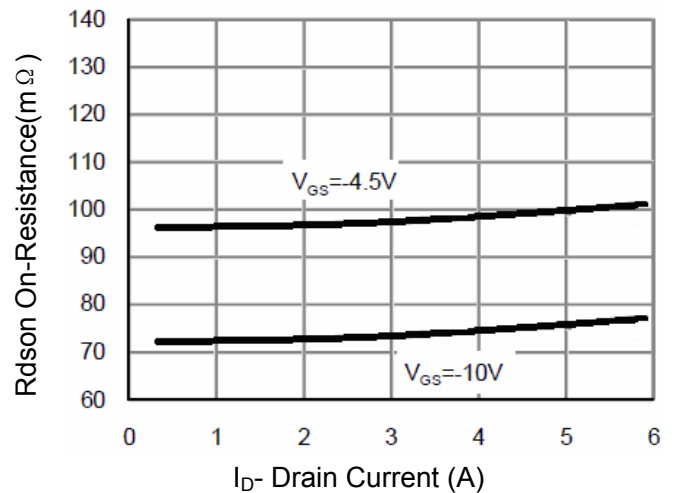
**Figure 3 Power Dissipation**



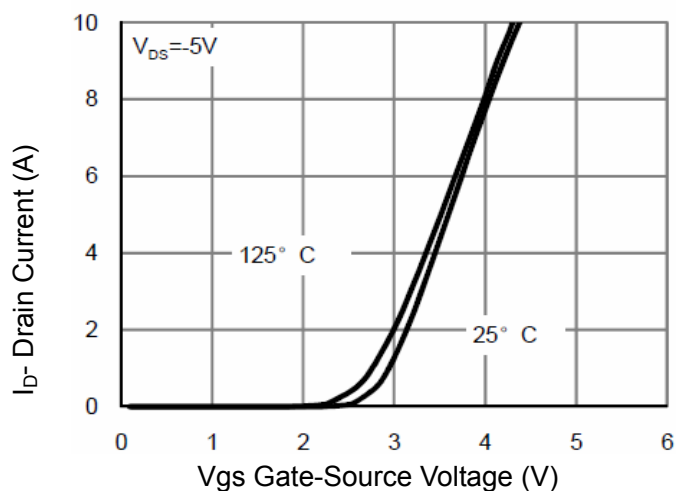
**Figure 4 Drain Current**



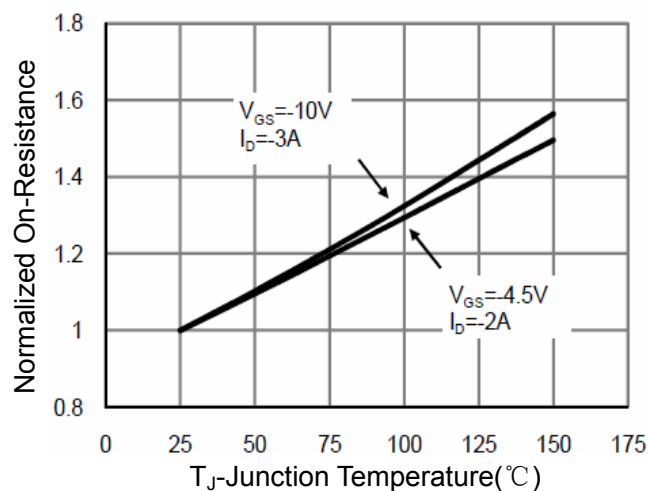
**Figure 5 Output Characteristics**



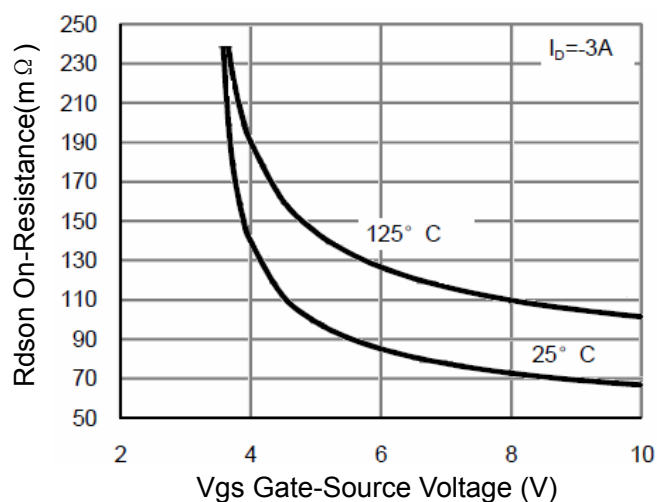
**Figure 6 Drain-Source On-Resistance**



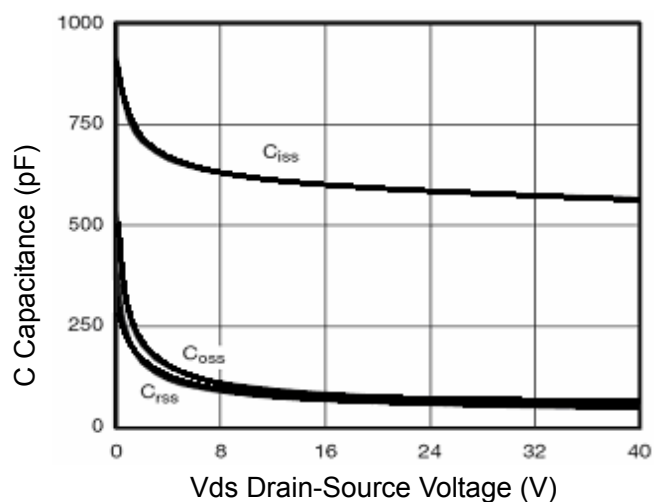
**Figure 7 Transfer Characteristics**



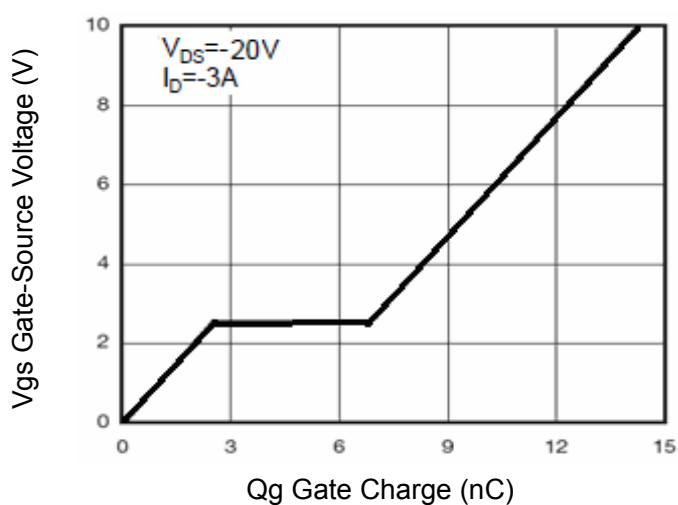
**Figure 8 Drain-Source On-Resistance**



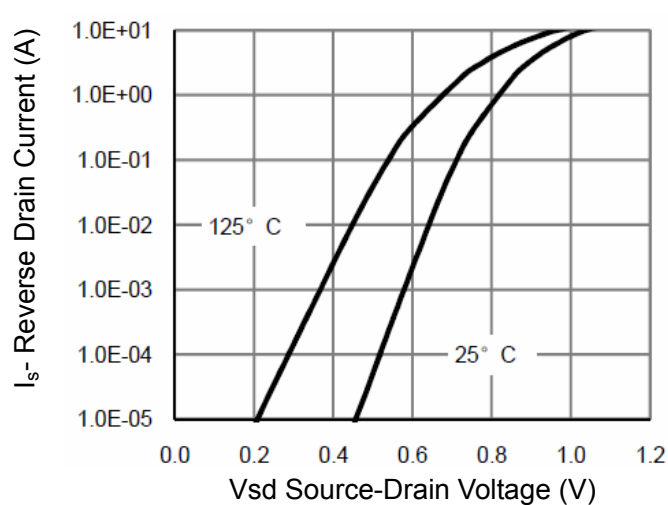
**Figure 9 Rdson vs Vgs**



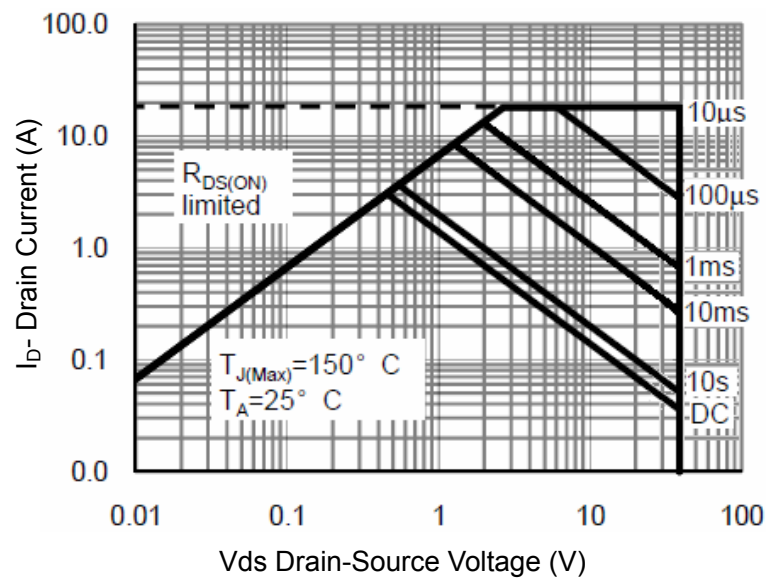
**Figure 10 Capacitance vs Vds**



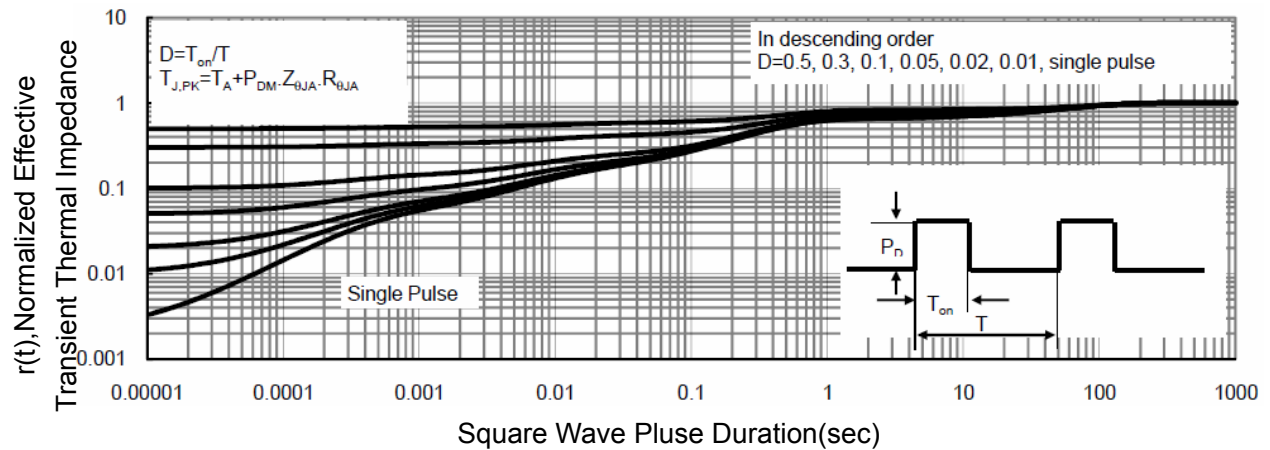
**Figure 11 Gate Charge**



**Figure 12 Source- Drain Diode Forward**

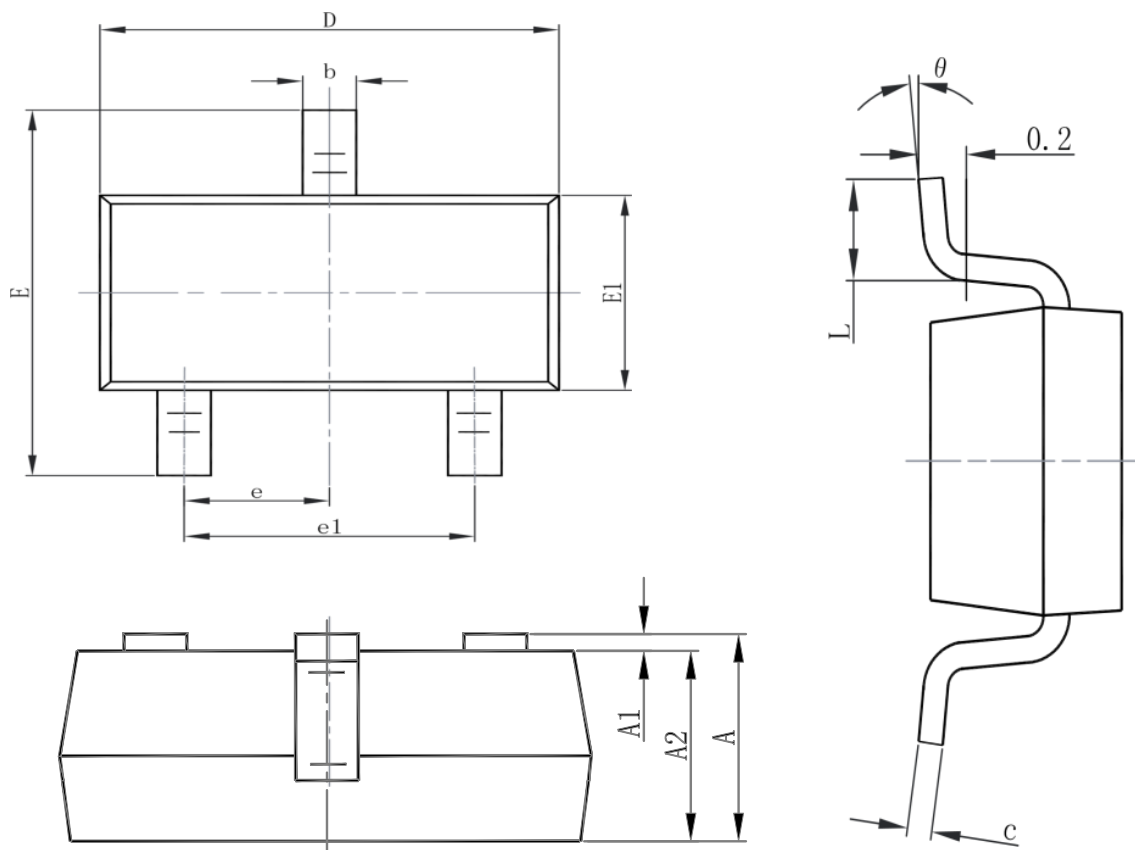


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

## Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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